



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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**CMXSH-3**

**SURFACE MOUNT  
TRIPLE ISOLATED  
SILICON SCHOTTKY DIODES**



[www.centrasemi.com](http://www.centrasemi.com)



**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXSH-3 type contains three (3) Isolated Schottky Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for applications requiring low forward voltage drop.

**MARKING CODE: XH3**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Peak Repetitive Reverse Voltage	$V_{RRM}$	30	V
Continuous Forward Current	$I_F$	100	mA
Peak Repetitive Forward Current	$I_{FRM}$	350	mA
Peak Forward Surge Current, $t_p=10\text{ms}$	$I_{FSM}$	750	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	357	$^\circ\text{C/W}$

**SYMBOL**

$V_{RRM}$	30	V
$I_F$	100	mA
$I_{FRM}$	350	mA
$I_{FSM}$	750	mA
$P_D$	350	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\theta_{JA}$	357	$^\circ\text{C/W}$

**UNITS**

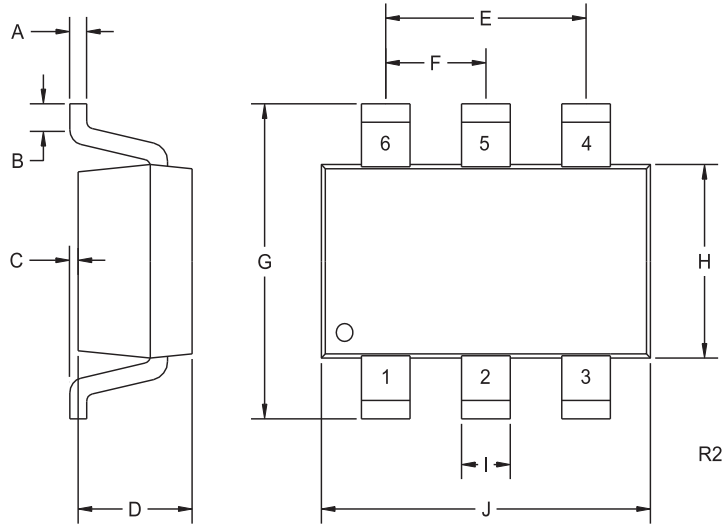
**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=25\text{V}$		90	500	nA
$I_R$	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	$\mu\text{A}$
$BV_R$	$I_R=100\mu\text{A}$	30			V
$V_F$	$I_F=2.0\text{mA}$		0.29	0.33	V
$V_F$	$I_F=15\text{mA}$		0.40	0.45	V
$V_F$	$I_F=100\text{mA}$		0.74	1.00	V
$C_T$	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

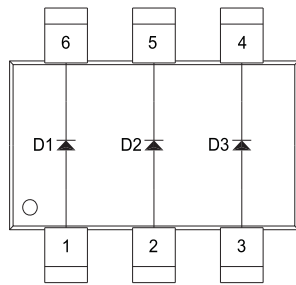
**CMXSH-3**  
**SURFACE MOUNT**  
**TRIPLE ISOLATED**  
**SILICON SCHOTTKY DIODES**



**SOT-26 CASE - MECHANICAL OUTLINE**



**PIN CONFIGURATION**



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

**LEAD CODE:**

- 1) Anode D1
- 2) Anode D2
- 3) Anode D3
- 4) Cathode D3
- 5) Cathode D2
- 6) Cathode D1

**MARKING CODE: XH3**

R5 (12-February 2010)